A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

Cancel claims 57-64, 68-73 and 75.

65. (Once Amended) An integrated circuit comprising:

a monocrystalline silicon substrate;

a roughened platinum layer over the substrate, the roughened platinum layer having a continuous surface characterized by columnar pedestals that are at least about 300Å tall; and

an intervening layer between the platinum layer and the substrate, the intervening layer comprising at least one of iridium, rhodium, ruthenium, platinum, palladium, osmium, silver, rhodium/platinum alloy, IrO_2, RuO_2, RhO_2, or OsO_2.

66. (Once Amended) The circuit of claim 65 wherein the pedestals terminate in dome-shaped tops.

67. (Once Amended) The circuit of claim 65 wherein the pedestals terminate in hemispherical tops.

74. (Once Amended) A capacitor comprising:

a first capacitor electrode over a monocrystalline silicon substrate;

a second capacitor electrode;

a dielectric layer between the first and second capacitor electrodes;

wherein both of the first and second capacitor electrodes comprise roughened platinum, the roughened platinum having a continuous surface characterized by columnar pedestals having heights greater than or equal to about one-third of a total thickness of the roughened platinum.

78. (new) The integrated circuit of claim 65 wherein the roughened platinum layer has a thickness of at least about 400Å.